Bulletin I20201 rev. A 09/98

International
IOR Rectifier

40HF(R) SERIES

STANDARD RECOVERY DIODES **Stud Version**

40 A

Features

- High surge current capability
- Designed for a wide range of applications
- Stud cathode and stud anode version
- Leaded version available
- Types up to 1600V V_{RRM}

TypicalApplications

- Battery charges
- Converters
- Power supplies
- Machine tool controls

Major Ratings and Characteristics

Parameters		40HF(R)		Units
		10 to 120	140 to 160	
$I_{F(AV)}$		40	40	A
	@ T_C	140	110	°C
$I_{F(RMS)}$		62		A
I_{FSM}	@ 50Hz	570		A
	@ 60Hz	595		A
I^2t	@ 50Hz	1600		A^2s
	@ 60Hz	1450		A^2s
V_{RRM}	range	100 to 1200	1400 to 1600	V
T_J	range	- 65 to 190	- 65 to 160	°C



case style
DO-203AB (DO-5)

ELECTRICAL SPECIFICATIONS

Voltage Ratings

Type number	Voltage Code	V_{RRM}, maximum repetitive peak reverse voltage V	V_{RSM}, maximum non-repetitive peak reverse voltage V	$V_{R(BR)}$, minimum avalanche voltage V **(1)**	I_{RRM} max. @ $T_J = T_J$ max. mA
40HF(R)	10	100	200	--	15
	20	200	300	--	
	40	400	500	500	
	60	600	720	725	9
	80	800	960	950	
	100	1000	1200	1150	
	120	1200	1440	1350	
	140	1400	1650	1550	4.5
	160	1600	1900	1750	

(1) Avalanche version only available from V_{RRM} 400V to 1600V.

Forward Conduction

Parameter		40HF(R) 10 to 120	40HF(R) 140 to 160	Units	Conditions		
$I_{F(AV)}$	Max. average forward current	40	40	A	180° conduction, half sine wave		
	@ Case temperature	140	110	°C			
$I_{F(RMS)}$	Max. RMS forward current	62		A			
P_R	Maximum non-repetitive peak reverse power	11		K·W	10µs square pulse, $T_J = T_J$ max. **see note (2)**		
I_{FSM}	Max. peak, one-cycle forward, non-repetitive surge current	570		A	t = 10ms	No voltage reapplied	Sinusoidal half wave, Initial $T_J = T_J$ max.
		595			t = 8.3ms		
		480			t = 10ms	100% V_{RRM} reapplied	
		500			t = 8.3ms		
I^2t	Maximum I^2t for fusing	1600		A^2s	t = 10ms	No voltage reapplied	
		1450			t = 8.3ms		
		1150			t = 10ms	100% V_{RRM} reapplied	
		1050			t = 8.3ms		
$I^2\sqrt{t}$	Maximum $I^2\sqrt{t}$ for fusing	16000		$A^2\sqrt{s}$	t = 0.1 to 10ms, no voltage reapplied		
$V_{F(TO)1}$	Low level value of threshold voltage	0.65		V	(16.7% x π x $I_{F(AV)}$ < I < π x $I_{F(AV)}$), $T_J = T_J$ max.		
$V_{F(TO)2}$	High level value of threshold voltage	0.70			(I > π x $I_{F(AV)}$), $T_J = T_J$ max.		
r_{f1}	Low level value of forward slope resistance	4.29		mΩ	(16.7% x π x $I_{F(AV)}$ < I < π x $I_{F(AV)}$), $T_J = T_J$ max.		
r_{f2}	High level value of forward slope resistance	3.98			(I > π x $I_{F(AV)}$), $T_J = T_J$ max.		
V_{FM}	Max. forward voltage drop	1.30		V	I_{pk}= 125A, T_J = 25°C, t_p = 400µs rectangular wave		

(2) Available only for Avalanche version, all other parameters the same as 40HF.

Thermal and Mechanical Specifications

Parameter		40HF(R)		Units	Conditions
		10 to 120	140 to 160		
T_J	Max. junction operating temperature range	-65 to 190	-65 to 160	°C	
T_{stg}	Max. storage temperature range	-65 to 190	-65 to 160		
R_{thJC}	Max. thermal resistance, junction to case	1.0		K/W	DC operation
R_{thCS}	Max. thermal resistance, case to heatsink	0.25			Mounting surface, smooth, flat and greased
T	Max. allowed mounting torque ±10%	2.3 - 3.4		Nm	Not lubricated threads
		20 - 30		lbf·in	
wt	Approximate weight	17 (0.6)		g (oz)	
	Case style	DO-203AB (DO5)			See Outline Table

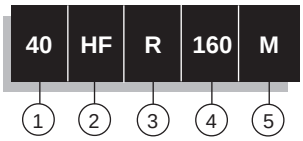
ΔR_{thJC} Conduction

(The following table shows the increment of thermal resistence R_{thJC} when devices operate at different conduction angles than DC)

Conduction angle	Sinusoidal conduction	Rectangular conduction	Units	Conditions
180°	0.14	0.10	K/W	$T_J = T_J$ max.
120°	0.16	0.17		
90°	0.21	0.22		
60°	0.30	0.31		
30°	0.50	0.50		

Ordering Information Table

Device Code



1 - 40 = Standard device
41 = Not isolated lead
42 = Isolated lead with silicone sleeve
(Red = Reverse polarity)
(Blue = Normal polarity)

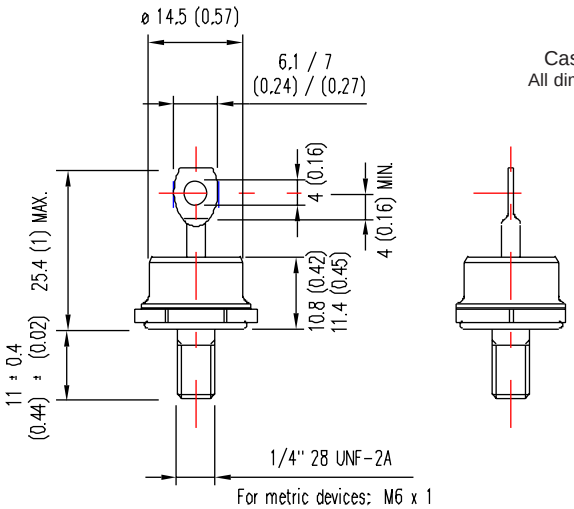
2 - HF = Standard diode
HA = Avalanche diode

3 - None = Stud Normal Polarity (Cathode to Stud)
R = Stud Reverse Polarity (Anode to Stud)

4 - Voltage code: Code x 10 = V_{RRM} (See Voltage Ratings table)

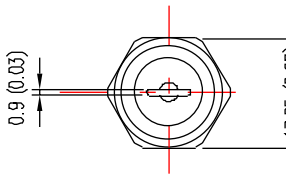
5 - None = Stud base DO-203AB (DO-5) 1/4" 28UNF-2A
M = Stud base DO-203AB (DO-5) M6 X 1 - (Not available for Avalanche diodes)

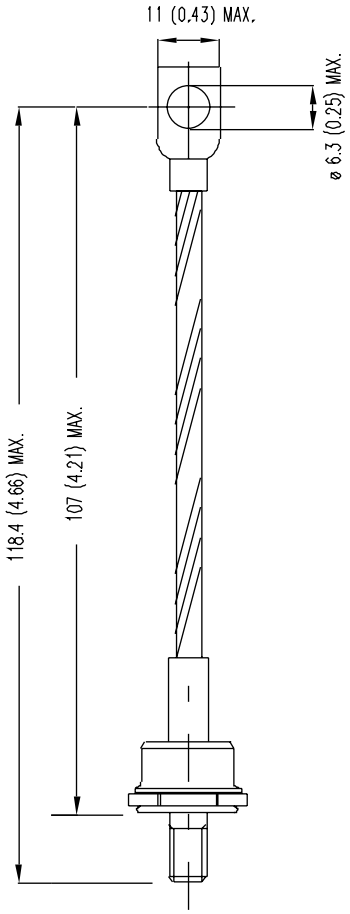
Outlines Table



40HF(R)

Case Style DO-203AB (DO-5)
All dimensions in millimeters (inches)





41HF(R)

Case Style DO-203AB (DO-5)
All dimensions in millimeters (inches)

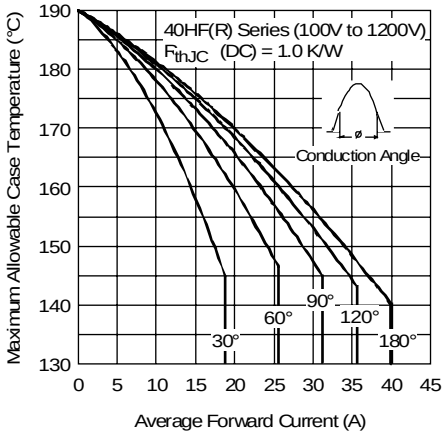


Fig. 1 - Current Ratings Characteristics

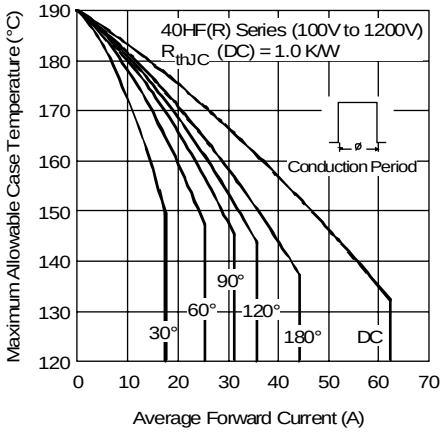


Fig. 2 - Current Ratings Characteristics

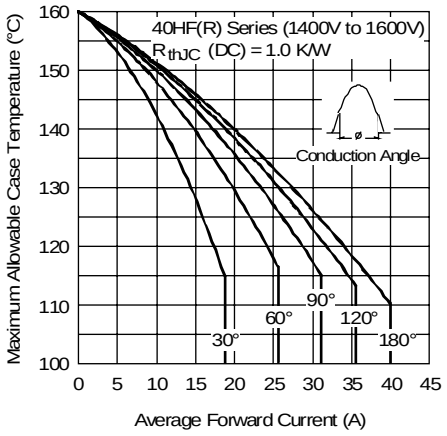


Fig. 3 - Current Ratings Characteristics

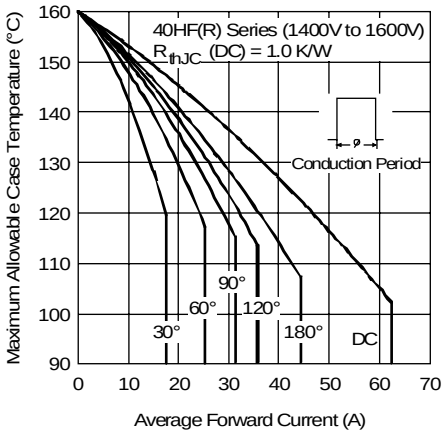


Fig. 4 - Current Ratings Characteristics

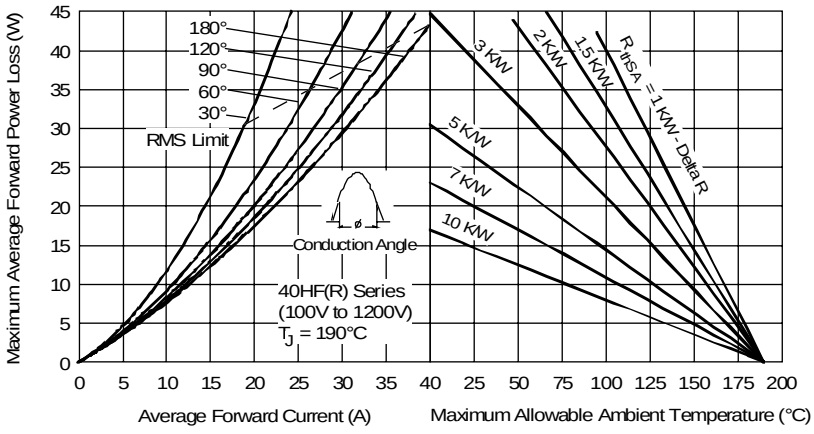


Fig. 5 - Forward Power Loss Characteristics

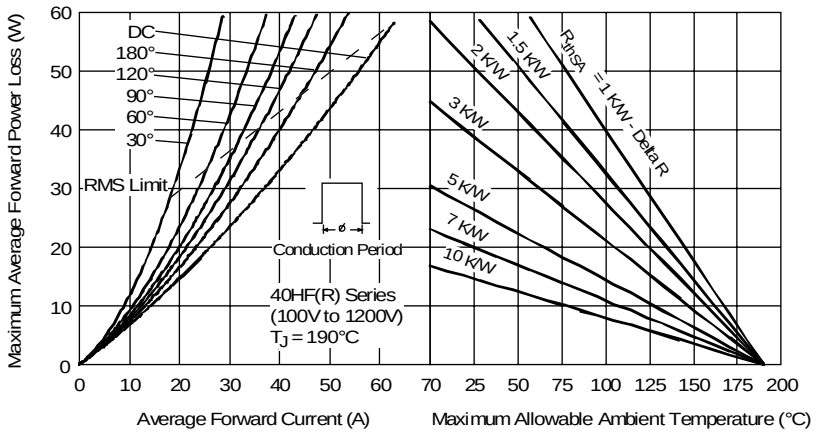


Fig. 6 - Forward Power Loss Characteristics

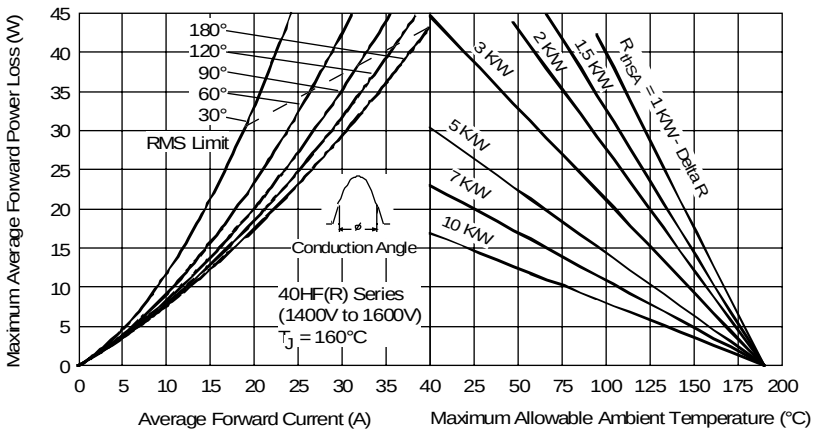


Fig. 7 - Forward Power Loss Characteristics

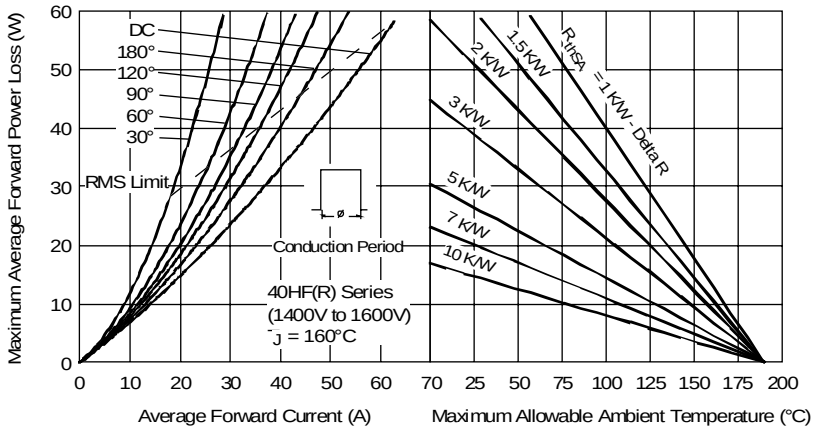


Fig. 8 - Forward Power Loss Characteristics

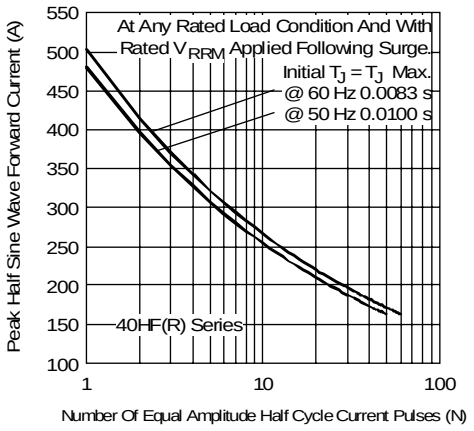


Fig. 9 - Maximum Non-Repetitive Surge Current

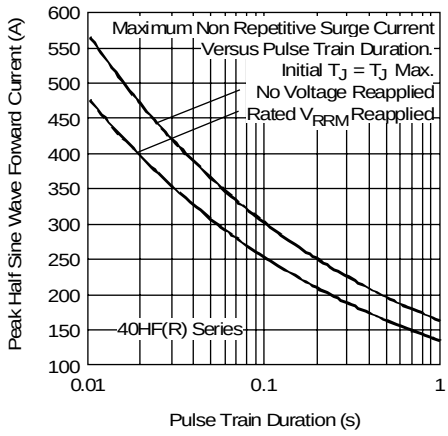


Fig. 10 - Maximum Non-Repetitive Surge Current

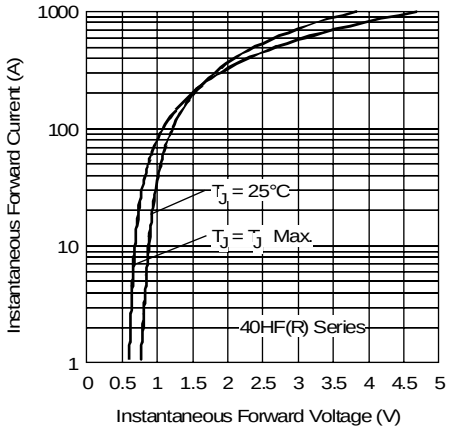


Fig. 11 - Forward Voltage Drop Characteristics

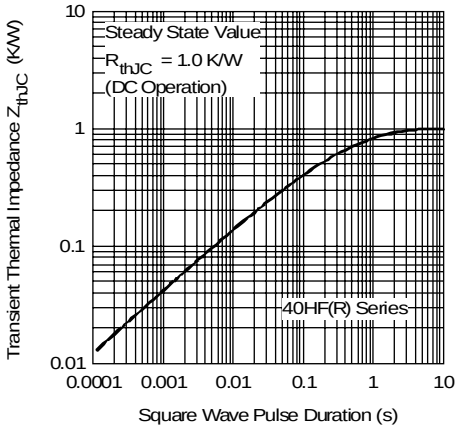


Fig. 12 - Thermal Impedance Z_{thJC} Characteristics

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